NSN 5962-01-370-0381

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Maximum Power Dissipation Rating:

1.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

An/fps-124

Features Provided:

Programmed

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Bipolar metal-oxide semiconductor

Case Outline Source And Designator:

D-9 mil-m-38510

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, digital, schottky, bipolar 8, 192 bit (1k x 8) programmable read-only memory (prom), monolithic silicon

Voltage Rating And Type Per Characteristic:

-0.5 volts total supply and 7.0 volts total supply and 4.5 volts positive power supply span and 5.5 volts positive power supply span

Time Rating Per Chacteristic:

45.00 nanoseconds access

Memory Device Type:

Prom

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Specification Data:

56232-1219252 manufacturers specification control

Specification Or Standard:

201 number

Departure From Cited Document:

Altered by programming, marking & testing

Shelf Life:

NI/o

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Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

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